

SEB161V-20
Schottky barrier diode

Revision:A

Features

- Power mold type. (CPD3)
- Low V_F
- High reliability

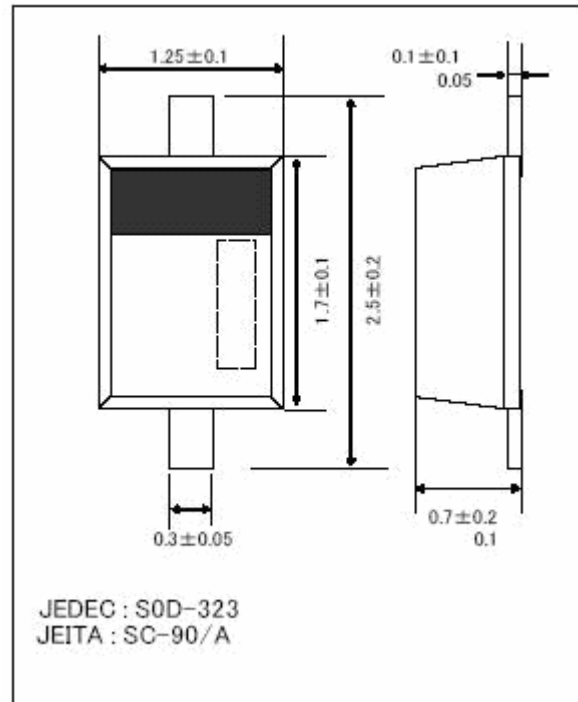
Applications

- General rectification

Construction

- Silicon epitaxial planer

● **External dimensions (Unit : mm)**



Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	25	V
Reverse voltage (DC)	V_R	20	V
Average rectified forward current	I_O	1	A
Forward current surge peak	T_{FSM}	30	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 ~ +125	°C

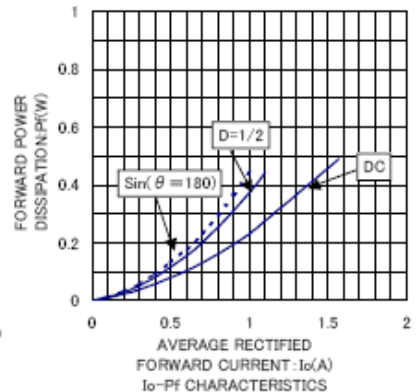
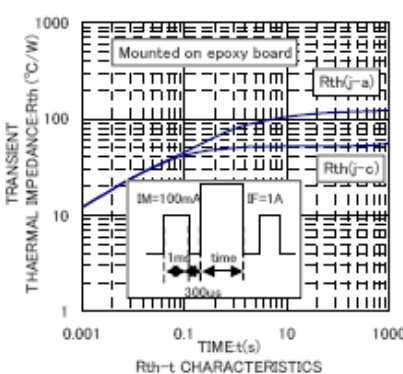
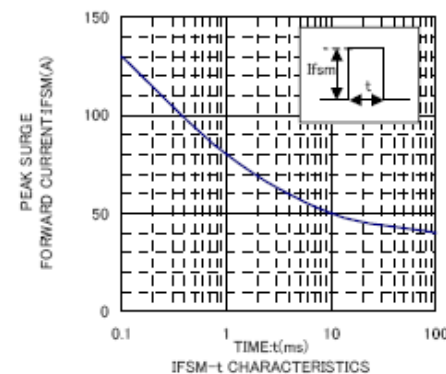
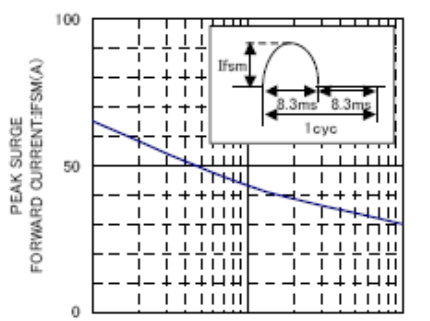
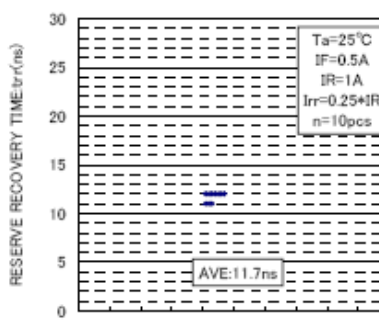
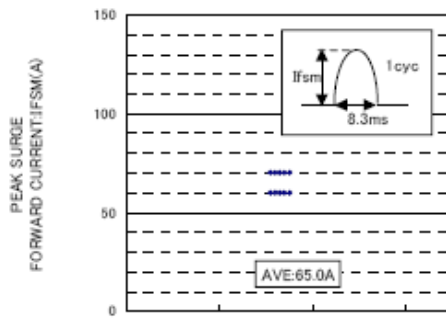
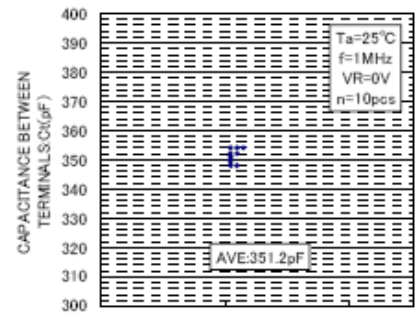
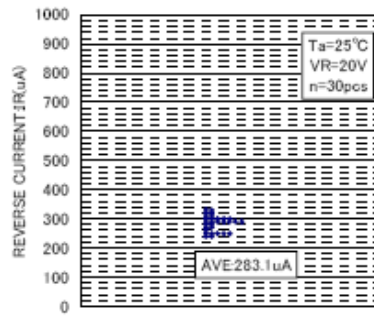
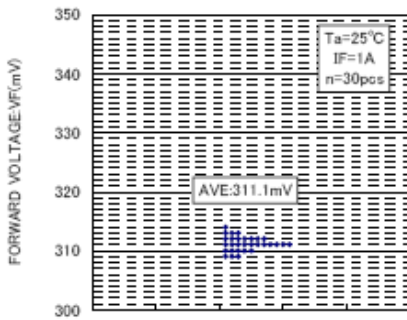
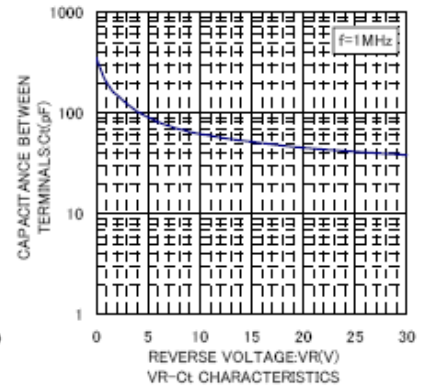
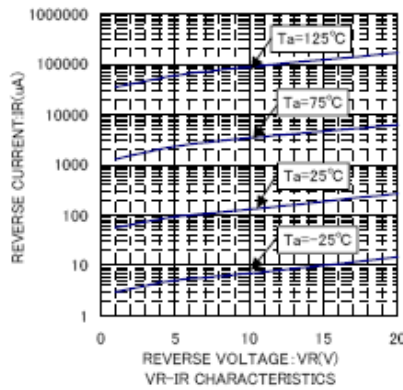
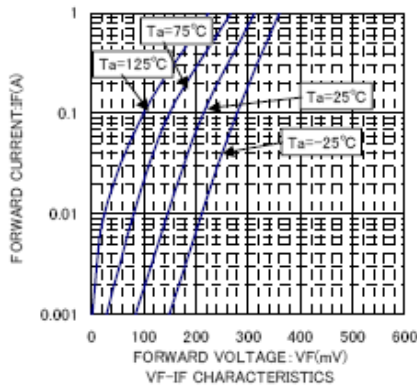
(*1) Mounted on epoxy board. 180°Half sine wave

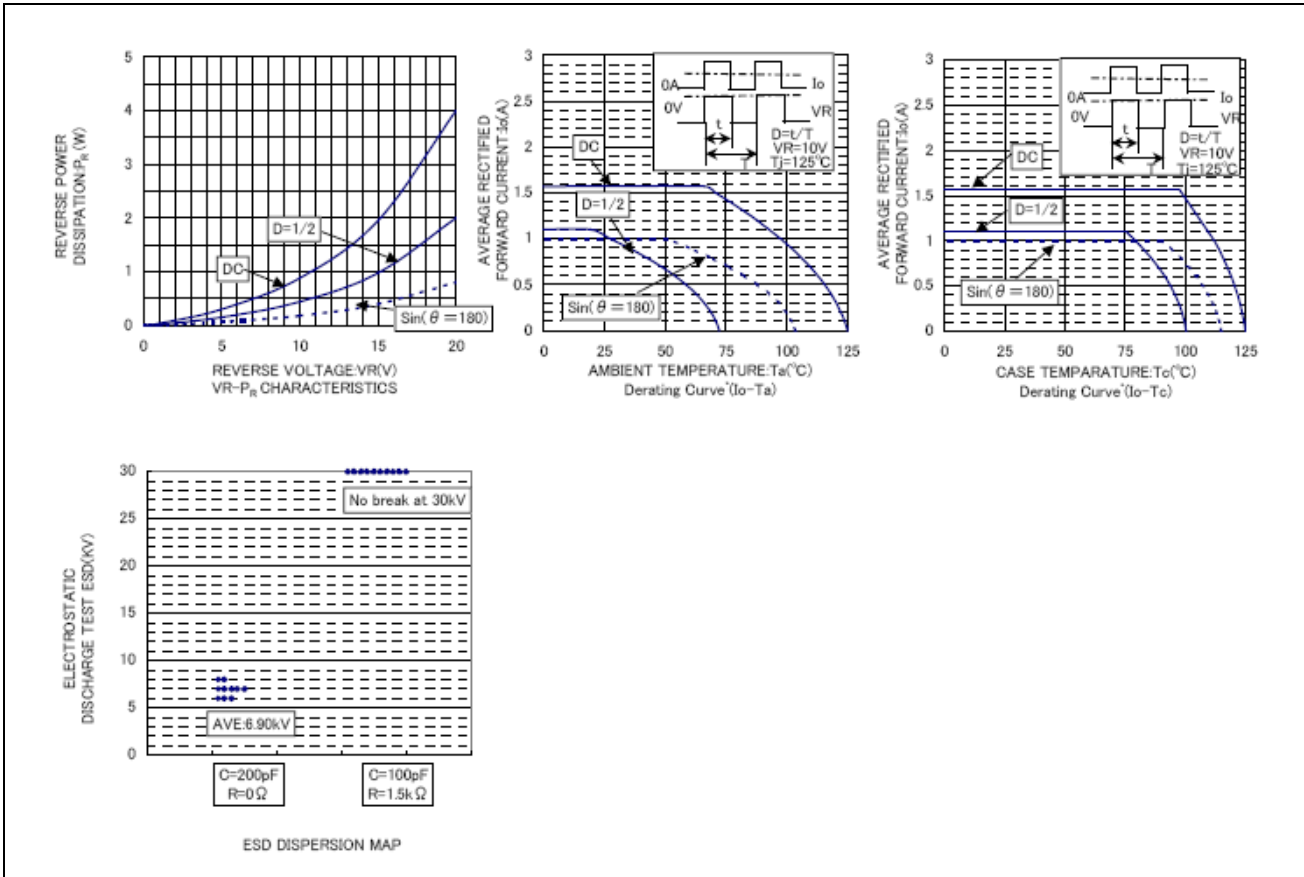
Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F2}		0.38	0.42	V	$I_F = 1.0A$
Reverse current	I_R	—	280	700	uA	$V_R = 20V$

- Please pay attention to static electricity when handling.

Electrical characteristic curves





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